

JUN 10 2004

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OFFICIAL

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of: Anthony *et al.*

Docket: TI-24953

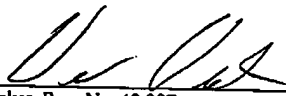
Serial No.: 09/116,138

Examiner: W. D. Coleman

Filed: 07/15/98

Art Unit: 2823

For: High Permittivity Silicate Gate Dielectric

<p>FACSIMILE CERTIFICATE</p> <p>I hereby certify that this correspondence is being transmitted by Facsimile to the Patent and Trademark Office in accordance with 37 C.F.R. §1.6d on June 10, 2004.</p> <p></p> <p>David Denker, Reg. No. 40,987</p>

FACSIMILE COVER SHEET

<input checked="" type="checkbox"/> FACSIMILE COVER SHEET (1 SHEET)	<input checked="" type="checkbox"/> AMENDMENT 1.111 (4 pages)
<input type="checkbox"/> NEW APPLICATION	<input type="checkbox"/> EOT (# Pages)
<input type="checkbox"/> DECLARATION	<input type="checkbox"/> NOTICE OF APPEAL (# Pages)
<input type="checkbox"/> ASSIGNMENT	<input type="checkbox"/> APPEAL (# Pages)
<input type="checkbox"/> FORMAL DRAWINGS	<input type="checkbox"/> ISSUE FEE
<input type="checkbox"/> INFORMAL DRAWINGS	<input type="checkbox"/> REPLY BRIEF (IN TRIPLICATE)
<input type="checkbox"/> CONTINUATION APP'N	
<input type="checkbox"/> DIVISIONAL APP'N	
NAME OF INVENTOR(S): Anthony <i>et al.</i>	
TITLE OF INVENTION: High Permittivity Silicate Gate Dielectric	
TI FILE NO.: TI-24953	DEPOSIT ACCT. NO.: 20-0668
FAXED: June 10, 2004 DUE: — ATTY/SECY: DD/tms	
RECEIPT DATE & SERIAL NO.: Appl. No.: 09/116,138 Filing Date: 07/15/98	

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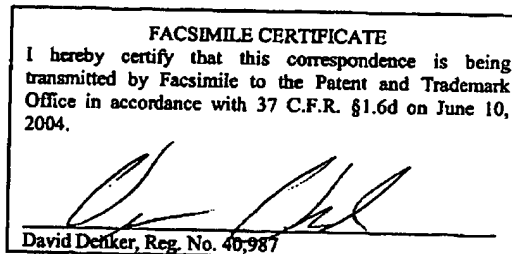
Art Unit: 2823

For: High Permittivity Silicate Gate Dielectric

CORRECTED REPLY PURSUANT TO 37 C.F.R. § 1.111

June 10, 2004

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450



Examiner:

During a recent review of the file, Applicants noticed that the amendment faxed on April 23, 2004 did not start the claim listing on a separate sheet. To correct this deficiency, this CORRECTED REPLY PURSUANT TO 37 C.F.R. § 1.111 is being sent as a complete replacement for the reply faxed April 23, 2004.

In response to the Office Action dated December 16, 2003, please amend the above-identified patent application as follows:

IN THE CLAIMS

- A. Please rejoin claims 28, 29, 46, 71, 72, and 73.
- B. Please replace the claims with the claims on the following sheets.
Claims 1 and 46 are amended below.
Withdrawn claims 2 - 25, 36 - 40, 47 - 70, and 74 - 80 are canceled below.
Claims 31 - 35 and 41 - 45 were canceled in a previous amendment.
With the rejoinder requested above, this leaves claims 1, 26 - 30, 46, and 71 - 73 active.